



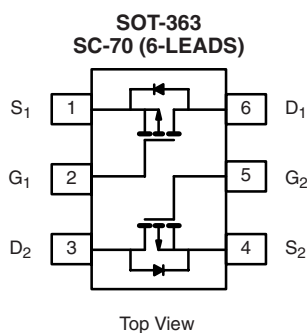
Dual P-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY

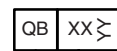
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 8	0.600 at $V_{GS} = - 4.5$ V	± 0.60
	0.850 at $V_{GS} = - 2.5$ V	± 0.50
	1.200 at $V_{GS} = - 1.8$ V	± 0.42

FEATURES

- TrenchFET[®] Power MOSFETs
- 1.8 V Rated

RoHS*
COMPLIANT

Marking Code

Lot Traceability
and Date Code

Part # Code

Ordering Information: Si1905DL-T1
Si1905DL-T1-E3 (Lead (Pb)-free)ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 8		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^a	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	± 0.60	± 0.57	A
	$T_A = 85\text{ }^{\circ}\text{C}$		± 0.43	± 0.41	
Pulsed Drain Current		I_{DM}	± 1.0		
Continuous Diode Current (Diode Conduction) ^a		I_S	- 0.25	- 0.23	
Maximum Power Dissipation ^a	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	0.30	0.27	W
	$T_A = 85\text{ }^{\circ}\text{C}$		0.16	0.14	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	360	415	°C/W
		400	460	
Maximum Junction-to-Foot (Drain)	R_{thJF}	300	350	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

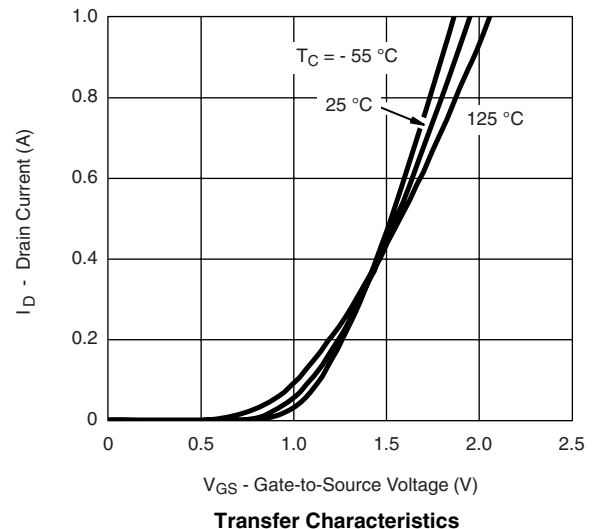
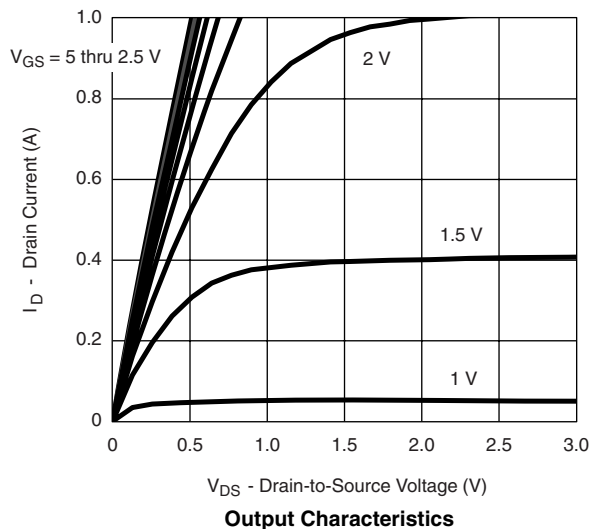
SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	- 0.45			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -6.4\text{ V}$, $V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -6.4\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 85\text{ }^{\circ}\text{C}$			- 5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}$, $V_{GS} = -4.5\text{ V}$	- 1.0			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\text{ V}$, $I_D = -0.57\text{ A}$		0.51	0.600	Ω
		$V_{GS} = -2.5\text{ V}$, $I_D = -0.48\text{ A}$		0.720	0.850	
		$V_{GS} = -1.8\text{ V}$, $I_D = -0.20\text{ A}$		1.0	1.200	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}$, $I_D = -0.57\text{ A}$		1.2		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -0.23\text{ A}$, $V_{GS} = 0\text{ V}$		- 0.8	- 1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -0.57\text{ A}$		1.5	2.3	nC
Gate-Source Charge	Q_{gs}			0.17		
Gate-Drain Charge	Q_{gd}			0.16		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}$, $R_L = 8\text{ }\Omega$ $I_D \equiv -0.5\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_G = 6\text{ }\Omega$		6	12	ns
Rise Time	t_r			25	50	
Turn-Off Delay Time	$t_{d(off)}$			10	20	
Fall Time	t_f			10	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -0.23\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		20	40	

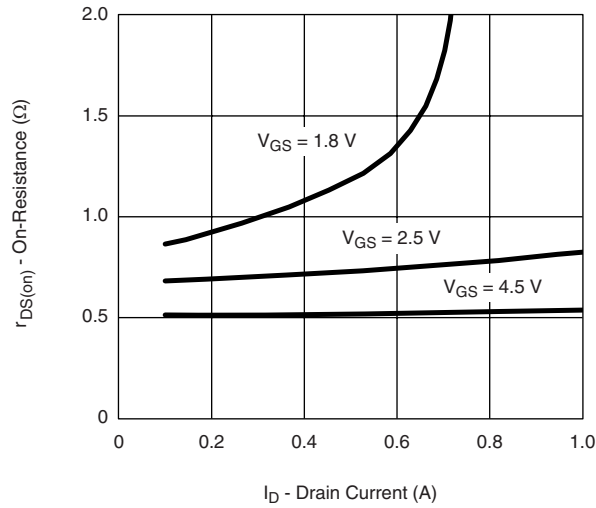
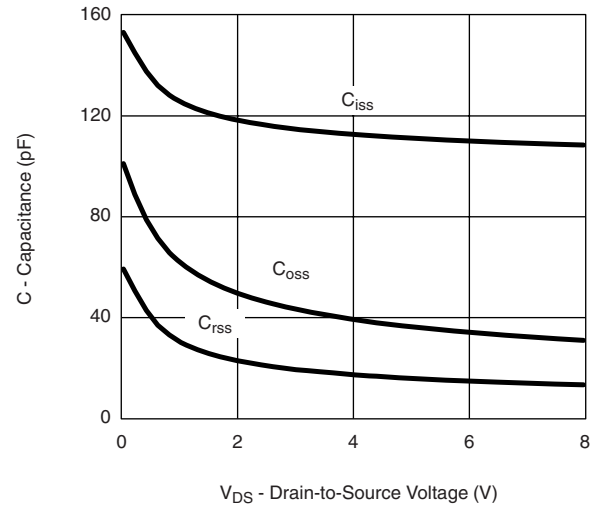
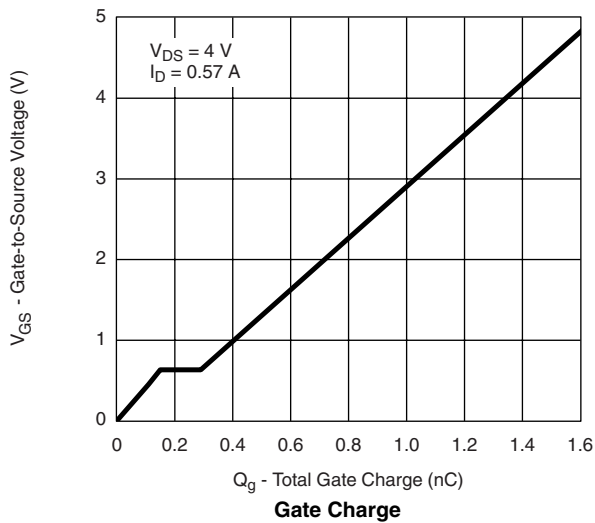
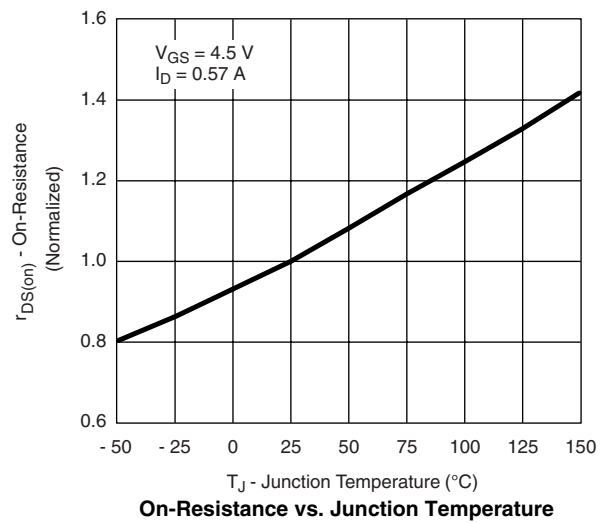
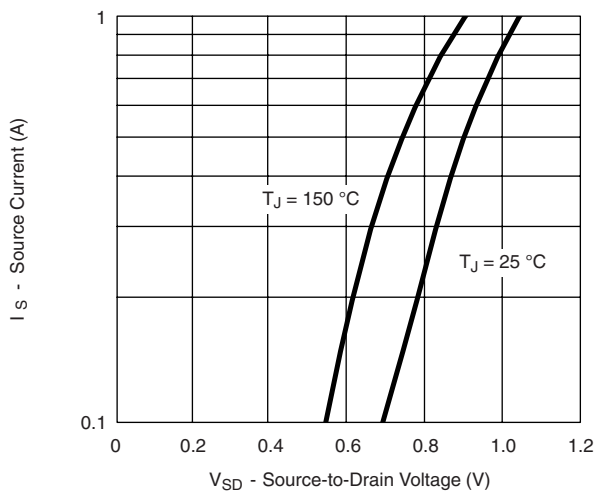
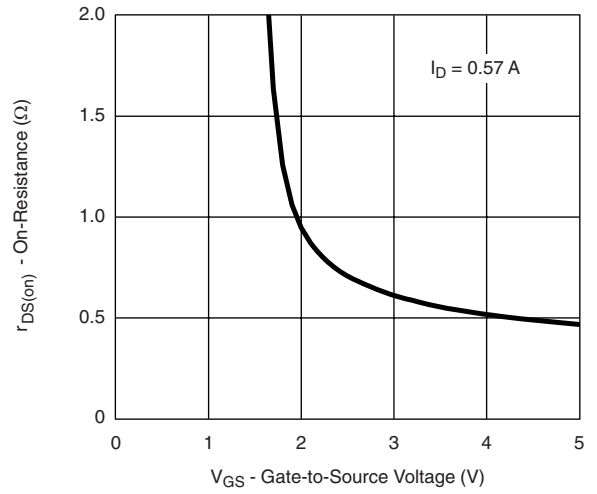
Notes:

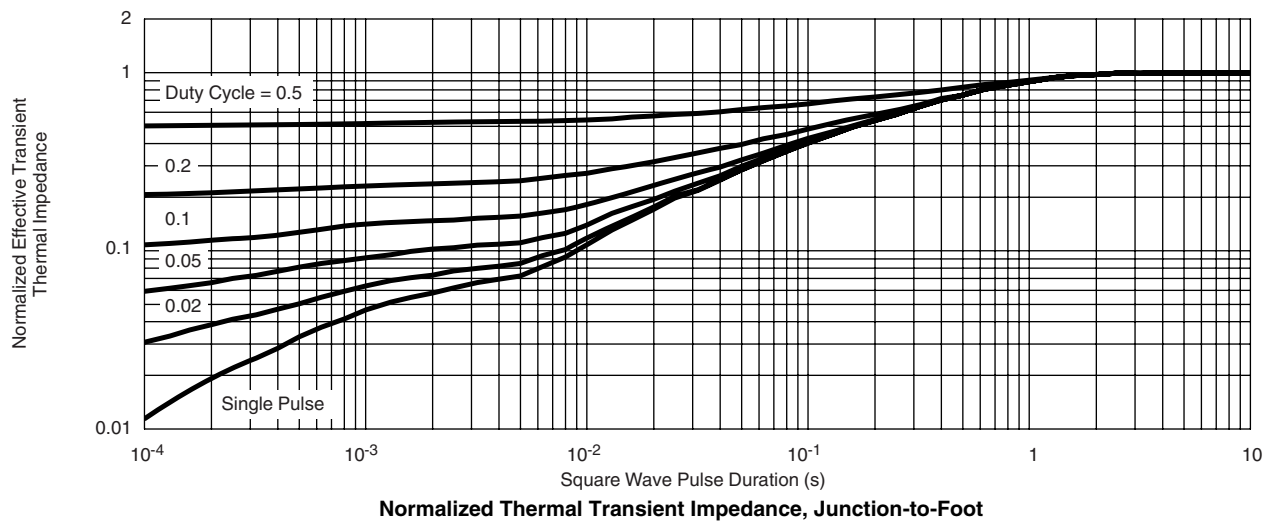
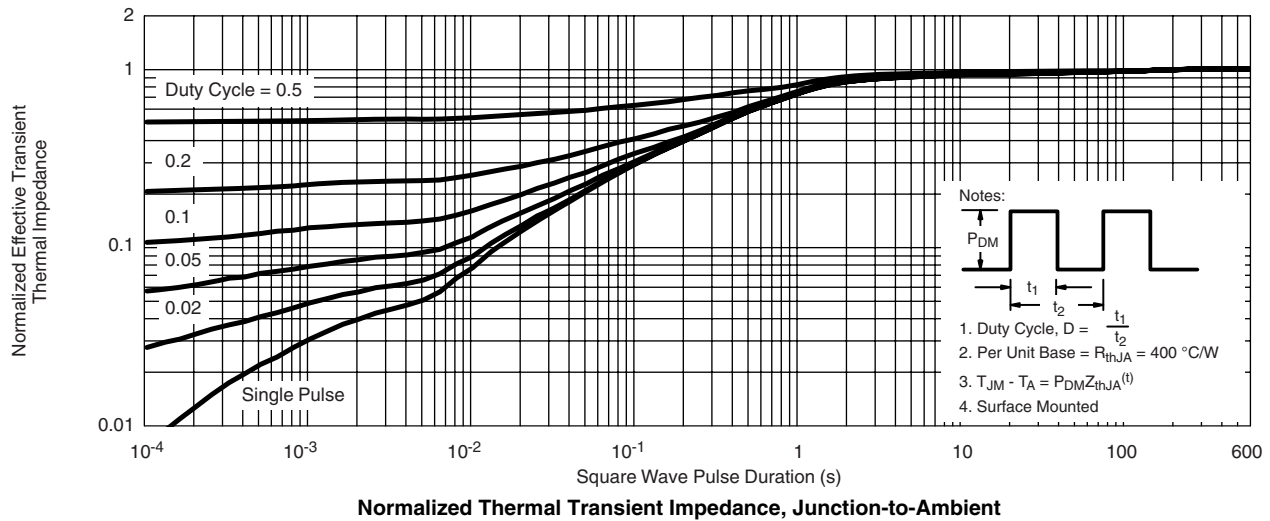
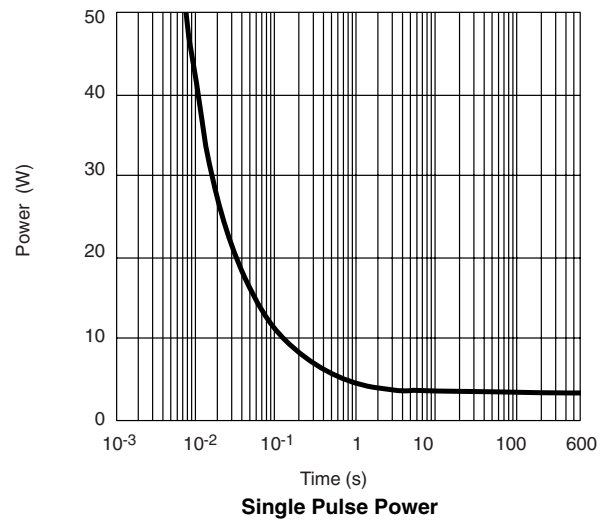
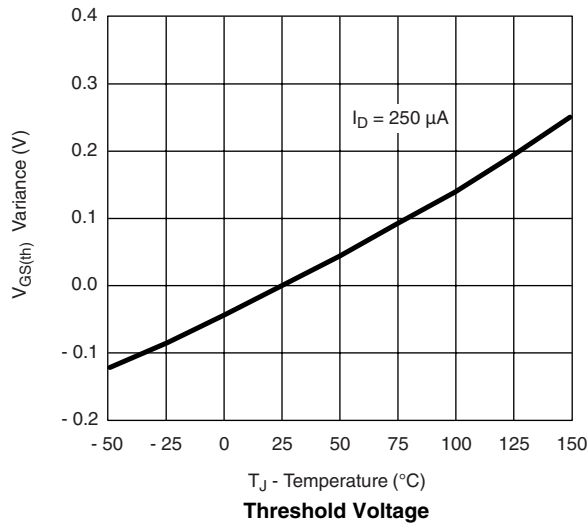
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage**

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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